

MJ N-Channel Enhancement Mode Power MOSFET

Description

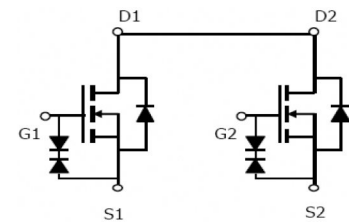
The MJ8601B uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

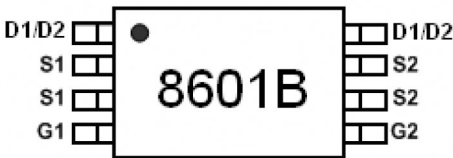
- ◆ $V_{DS} = 30V, I_D = 8A$
 $R_{DS(ON)} < 26m\Omega @ V_{GS} = 4.5V$
 $R_{DS(ON)} < 21m\Omega @ V_{GS} = 10V$
ESD Rating: 2000V HBM
- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Application

- ◆ PWM application
- ◆ Load switch



Schematic diagram



Marking and pin Assignment



TSSOP-8 top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
8601B	MJ8601B	TSSOP-8	Ø330mm	12mm	3000 units

Absolute Maximum Ratings (Tc =25 °Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±12	V
Drain Current-Continuous	I_D	8	A
Pulsed Drain Current (Note 1)	I_{DM}	32	A
Maximum Power Dissipation	P_D	1.5	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient (Note 2)	$R_{\theta JA}$	83	°C/W
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Electrical Characteristics (T_A =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	30	34.5	37	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =±10V,V _{DS} =0V	-	-	±10	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	0.55	0.7	0.95	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A	-	15	21	mΩ
		V _{GS} =4.5V, I _D =5.5A	-	18	26	mΩ
Forward Transconductance	g _{FS}	V _{DS} =5V,I _D =8A	-	20	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C _{iss}	V _{DS} =15V,V _{GS} =0V, F=1.0MHz	-	870	-	PF
Output Capacitance	C _{oss}		-	130	-	PF
Reverse Transfer Capacitance	C _{rss}		-	100	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =15V,R _L =1.25Ω V _{GS} =10V,R _{GEN} =3Ω	-	5		nS
Turn-on Rise Time	t _r		-	3.5		nS
Turn-Off Delay Time	t _{d(off)}		-	19		nS
Turn-Off Fall Time	t _f		-	3.5		nS
Total Gate Charge	Q _g	V _{DS} =15V,I _D =8A, V _{GS} =4.5V	-	15		nC
Gate-Source Charge	Q _{gs}		-	2.5	-	nC
Gate-Drain Charge	Q _{gd}		-	3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =8A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	8	A

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t ≤ 10 sec.
③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
④ Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

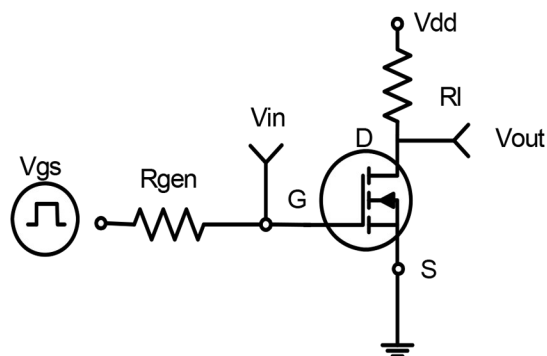


Figure 1 Switching Test Circuit

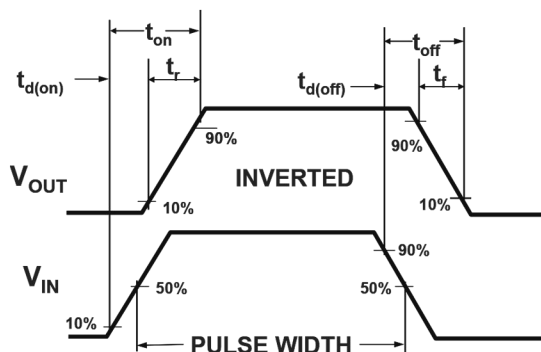


Figure 2 Switching Waveforms

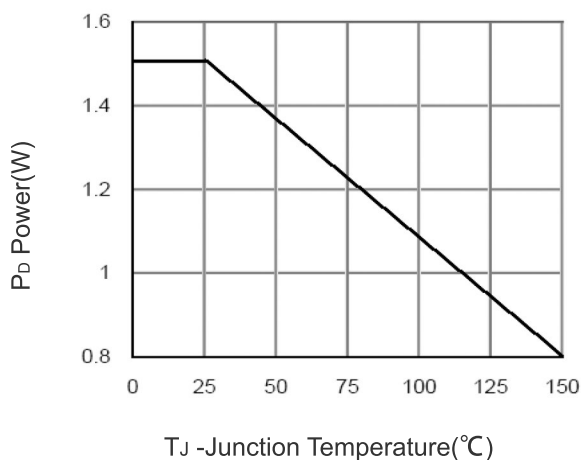


Figure 3 Power Dissipation

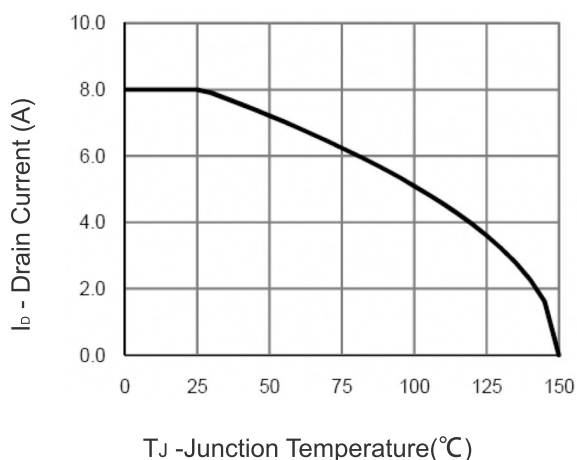


Figure 4 Drain Current

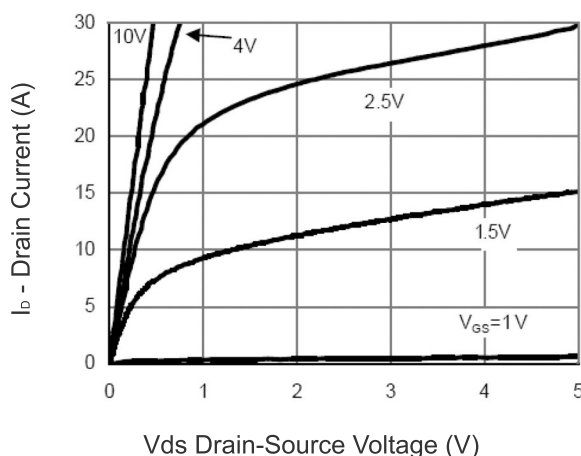


Figure 5 Output Characteristics

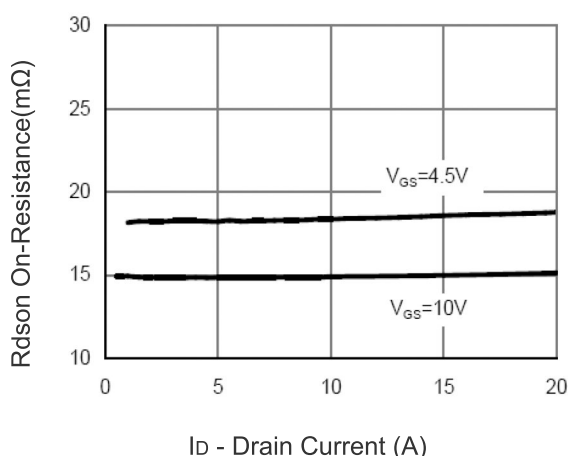
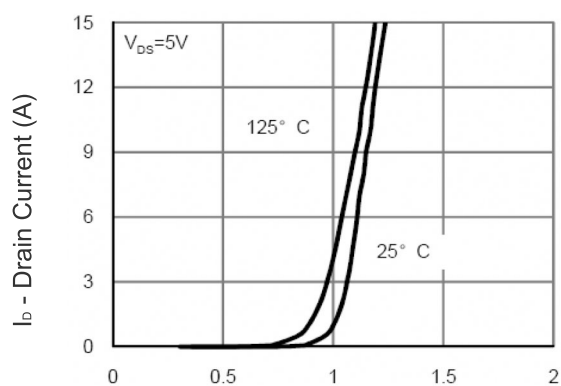
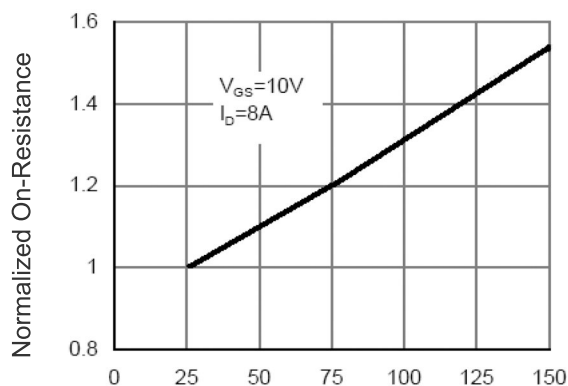


Figure 6 Drain-Source On-Resistance



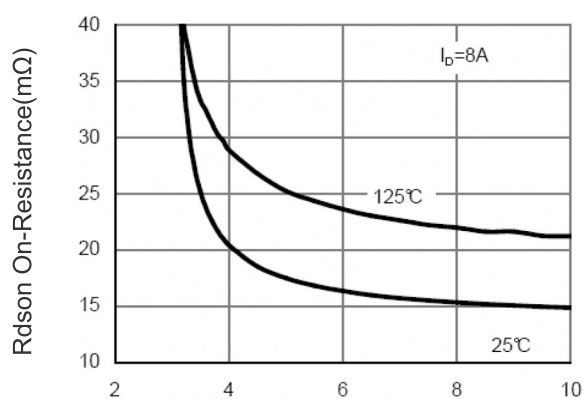
V_{GS} Gate-Source Voltage (V)

Figure 7 Transfer Characteristics



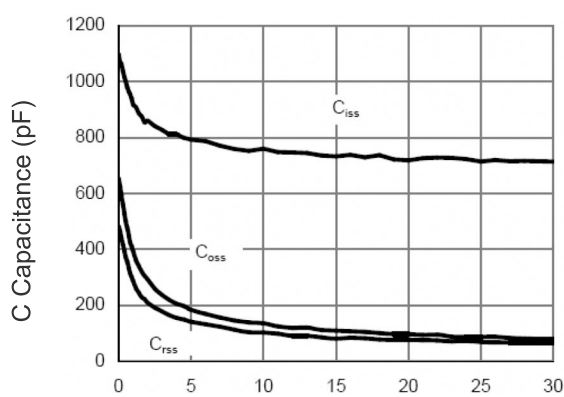
T_J -Junction Temperature(°C)

Figure 8 Drain-Source On-Resistance



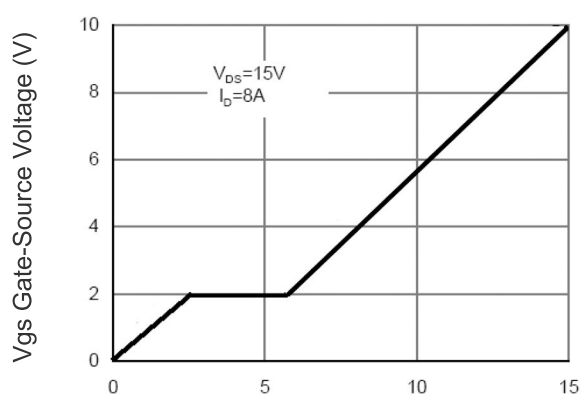
V_{GS} Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs



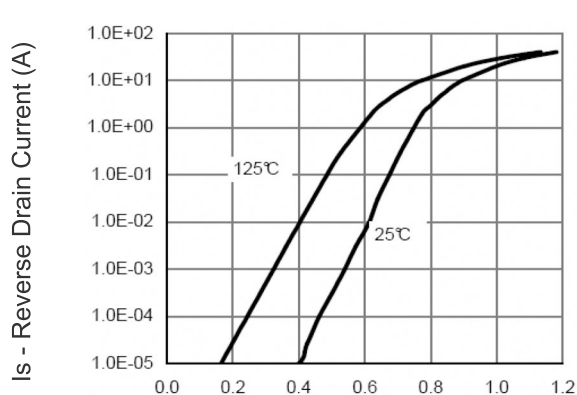
V_{DS} Drain-Source Voltage (V)

Figure 10 Capacitance vs Vds



Q_g Gate Charge (nC)

Figure 11 Gate Charge



V_{SD} Source-Drain Voltage (V)

Figure 12 Source- Drain Diode Forward

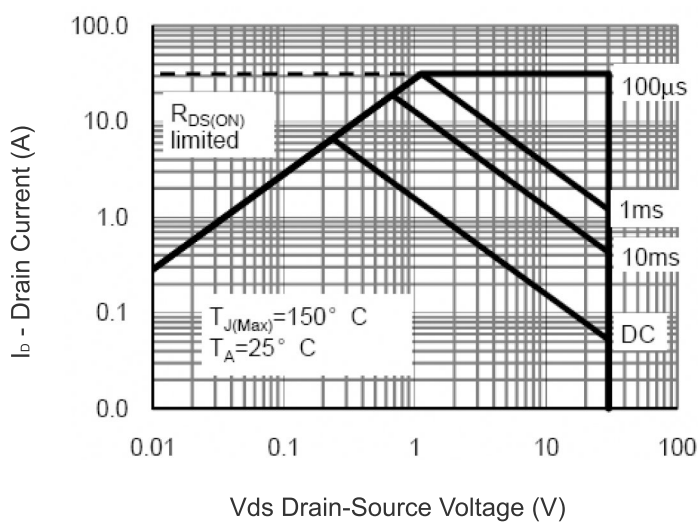


Figure 13 Safe Operation Area

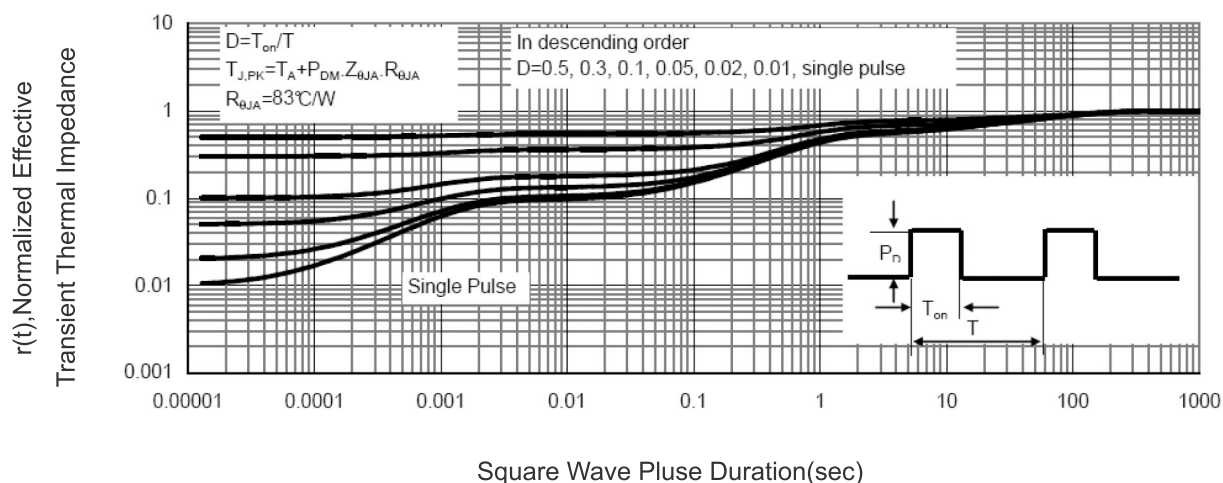
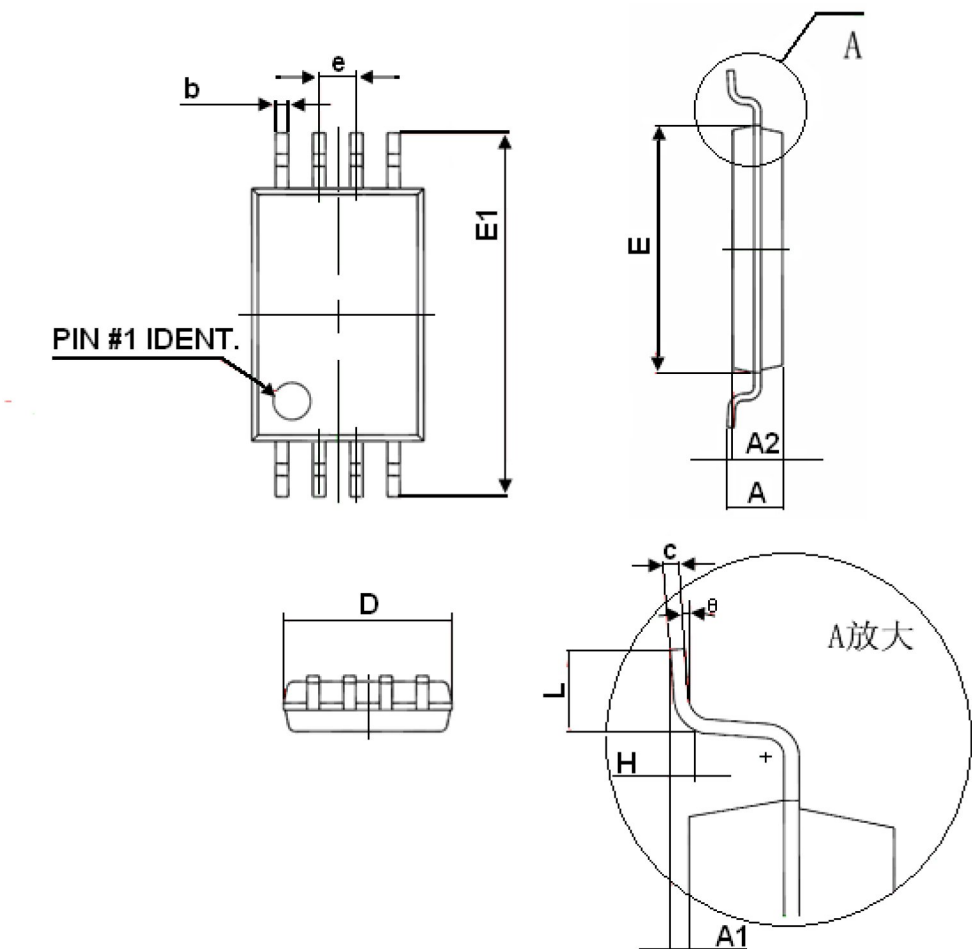


Figure 14 Normalized Maximum Transient Thermal Impedance

Tssop-8 Package Information



Symbol	Dimensions In Millimeters	
	Min	Max
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.100
A2	0.800	1.000
A1	0.020	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°

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